

- ✓ **Better Efficiency**
- ✓ **High Reliability**
- ✓ **Superior Quality**
- ✓ **Very Good Aesthetics**

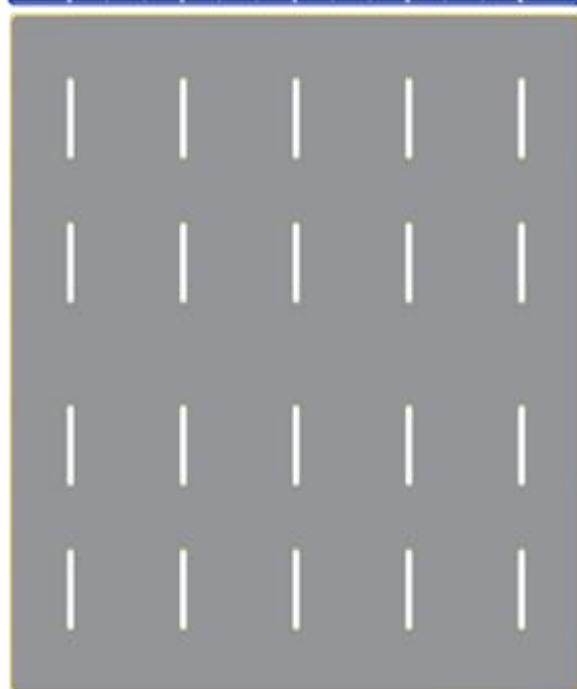
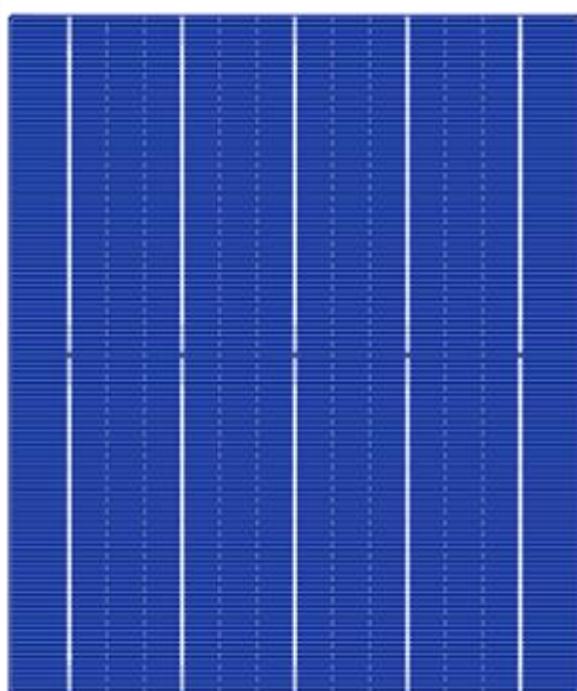
Size:
 158.75 x 158.75 mm
 Thickness:
 160±20 um

Available in 5 BB

Key Features

- Mainstream front and back electrode design, strong adaptability of the module side, compatible with half-cell modules
- In-depth optimization of the thermal oxidation process and PE coating process for the front to ensure excellent PID resistance
- Designed with a solid front bus bar and long back electrode, mainstream wafers, processed for low wafer thickness loss and low thermal stress, giving the product exceptional mechanical load performance
- Mainstream light-induced degradation (LID) equipment to ensure high resistance to LID
- Fully automated appearance, EL, and electrical performance testing equipment to ensure stable quality

G1-PERC Cell



Eff(%)	Pmpp(Pmax)	Voc	Isc	Vmpp(Vmp)	Impp(Imp)
21.5	5.42	0.670	10.14	0.565	9.59
21.6	5.44	0.671	10.14	0.566	9.61
21.7	5.47	0.672	10.16	0.568	9.63
21.8	5.49	0.673	10.17	0.569	9.65
21.9	5.52	0.674	10.18	0.571	9.67
22.0	5.54	0.675	10.18	0.573	9.67
22.1	5.57	0.676	10.19	0.575	9.69
22.2	5.59	0.677	10.19	0.577	9.69
22.3	5.62	0.678	10.20	0.579	9.71
22.4	5.64	0.679	10.21	0.580	9.73
22.5	5.67	0.680	10.23	0.582	9.75
22.6	5.70	0.681	10.25	0.583	9.77
22.7	5.72	0.682	10.27	0.584	9.79

- Under standard test condition : 1000W / m² , AM 1.5 , 25°C ● Illustration : 21.6% → actual range 21.6%~21.69%
- Specification and data are for reference only and may change without prior notice.